

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CDH300
CDH333

SILICON LOW LEAKAGE DIODE

JEDEC D0-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CDH300, CDH333 types are epitaxial planar silicon diodes designed for low leakage, high conductance applications. Higher breakdown voltage devices are available on special order.

MAXIMUM RATING (T_A=25°C)

	SYMBOL		UNIT
Peak Repetitive Reverse Voltage	VRRM	150	V
Peak Working Reverse Voltage	VRWM	125	V
Average Forward Current	I _O	200	mA
Forward Steady-State Current	I _F	500	mA
Recurrent Peak Forward Current	i _f	600	mA
Peak Forward Surge Current (1.0s pulse)	I _{FSM}	1000	mA
Peak Forward Surge Current (1.0μs pulse)	I _{FSM}	4000	mA
Power Dissipation	P _D	500	mW
Operating and Storage Junction Temperature	T _J , T _{STG}	-65 TO +200	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CDH300		CDH333		UNIT
		MIN	MAX	MIN	MAX	
I _R	V _R =125V		1.0		3.0	nA
I _R	V _R =125V, T _A =100°C		-		500	nA
I _R	V _R =125V, T _A =150°C		3.0		-	μA
B _{VR}	I _R =100μA	150		150		V
V _F	I _F =1.0mA		0.70		-	V
V _F	I _F =5.0mA		0.78		-	V
V _F	I _F =10mA		0.80		-	V
V _F	I _F =50mA		0.88	0.80	0.89	V
V _F	I _F =100mA		0.92	0.83	0.94	V
V _F	I _F =150mA		-	0.86	0.97	V
V _F	I _F =200mA		1.0	0.87	1.05	V
V _F	I _F =250mA		-	0.88	1.08	V
V _F	I _F =300mA		-	0.90	1.15	V
C	V _R =0V		6.0		6.0	pF
t _{rr}	I _F =I _R =10mA, Recov. to 1.0mA	1.0 TYP	3.0	1.0 TYP	3.0	μs